

## TSM1NB60CH C5G

#### **TSM1NB60CH C5G Information**

Heisener.com

Part Number TSM1NB60CH C5G Manufacturer TSC America Inc.

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

DescriptionMOSFET, SINGLE, N-CHANNEL, PLANAPackageTO-251-3 Short Leads, IPak, TO-251AA

For the pricing/inventory/lead time, please contact

us

For Reference Only

Website: https://www.heisener.com
E-mail: salesdept@heisener.com



Request a Quote

# **Certified Quality**

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









# **TSM1NB60CH C5G Specifications**

Manufacturer Part Number  Manufacturer  TSC America Inc.  Discrete Semiconducto  Transistors - FETs, MC  Package  TO-251-3 Short Leads,  Series  - FET Type  N-Channel  Technology  MOSFET (Metal Oxide  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  TSM1NB60CH C5G  TSC America Inc.  Discrete Semiconducto  Transistors - FETs, MC  To-251-3 Short Leads,  -  HOSFET (Metal Oxide  100V	
Category  Discrete Semiconducto Transistors - FETs, MC  Package  TO-251-3 Short Leads, Series  - FET Type  N-Channel  Technology  MOSFET (Metal Oxide Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  Discrete Semiconducto Transistors - FETs, MC  N-Channel  N-Channel  MOSFET (Metal Oxide 1A (Tc)	
Transistors - FETs, MC Package TO-251-3 Short Leads, Series - FET Type N-Channel Technology MOSFET (Metal Oxide Drain to Source Voltage (Vdss) 600V Current - Continuous Drain (Id) @ 25°C 1A (Tc)	
Package TO-251-3 Short Leads, Series - FET Type N-Channel Technology MOSFET (Metal Oxide Drain to Source Voltage (Vdss) 600V Current - Continuous Drain (Id) @ 25°C 1A (Tc)	r Products
Series - N-Channel  Technology MOSFET (Metal Oxide  Drain to Source Voltage (Vdss) 600V  Current - Continuous Drain (Id) @ 25°C 1A (Tc)	OSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide Drain to Source Voltage (Vdss) 600V Current - Continuous Drain (Id) @ 25°C 1A (Tc)	, IPak, TO-251AA
Technology MOSFET (Metal Oxide Drain to Source Voltage (Vdss) 600V  Current - Continuous Drain (Id) @ 25°C 1A (Tc)	
Drain to Source Voltage (Vdss) 600V Current - Continuous Drain (Id) @ 25°C 1A (Tc)	
Current - Continuous Drain (Id) @ 25°C 1A (Tc)	e)
Drive Voltage (Max Rds On, Min Rds On) 10V	
Vgs(th) (Max) @ Id 4.5V @ 250µA	
Gate Charge (Qg) (Max) @ Vgs 6.1nC @ 10V	
Input Capacitance (Ciss) (Max) @ Vds 138pF @ 25V	
Vgs (Max) ±30V	
FET Feature -	
Power Dissipation (Max) 39W (Tc)	
Rds On (Max) @ Id, Vgs 10 Ohm @ 500mA, 10	V
Operating Temperature $-55^{\circ}\text{C} \sim 150^{\circ}\text{C} \text{ (TJ)}$	
Mounting Type Through Hole	
Supplier Device Package TO-251 (IPAK)	
Package / Case TO-251-3 Short Leads,	
	IPak, TO-251AA

#### TSM1NB60CH C5G Guarantees



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### TSM1NB60CH C5G Payment Methods



















### TSM1NB60CH C5G Shipping Methods













If you have any question about TSM1NB60CH C5G, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com